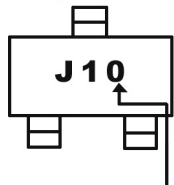
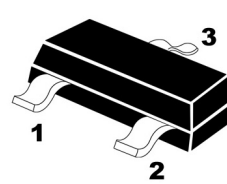
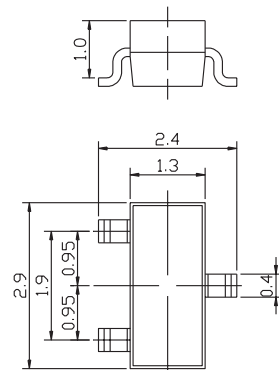


**TRANSISTOR (PNP)**
**Plastic-Encapsulate Transistor**

<p><b>FEATURES</b></p> <p>Power dissipation  <math>P_{CM} : 0.2W</math> (<math>T_{amb}=25^{\circ}C</math>)</p> <p>Collector current  <math>I_{CM} : -0.8A</math></p> <p>Collector-base Voltage  <math>V_{(BR)CBO} : -30 V</math></p> <p>Operating and storage junction temperature range  <math>T_J, T_{stg} : -55^{\circ}C</math> to <math>+150^{\circ}C</math></p> <p style="text-align: center;">Marking</p> <div style="text-align: center;">  <p>hFE grade</p> </div>	<p><b>SOT-23</b></p> <ol style="list-style-type: none"> <li>1. BASE</li> <li>2. EMITTER</li> <li>3. COLLECTOR</li> </ol> <div style="text-align: right;">  </div> <div style="text-align: center;">  <p style="text-align: right;">Unit:mm</p> </div>
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**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**  
 Ratings at 25°C ambient temperature unless otherwise specified.

**ELECTRICAL CHARACTERISTICS**

Parameters	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100 \mu A, I_E=0$		-30	V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-10mA, I_B=0$	-25		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-1mA, I_C=0$	-5		V
Collector cut-off current	$I_{CBO}$	$V_{CB}=-30V, I_E=0$		-100	$\mu A$
Emitter cut-off current	$I_{EBO}$	$V_{EB}=-5V, I_C=0$		-100	$\mu A$
DC current gain	$h_{FE(1)}$	$V_{CE}=-1V, I_C=-100mA$	100	320	
	$h_{FE(2)}$	$V_{CE}=-1V, I_C=-800mA$	40		
Collector-emitter saturation voltage	$V_{CEsat}$	$I_C=-500mA, I_B=-20mA$		-0.4	V

**CLASSIFICATION OF  $h_{FE(1)}$** 

Rank	O	Y
Range	100-200	160-320

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